SS510BFL

SMBF Schottky Barrier Rectifier Diode　肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Built-in strain relief 内应力释放
Surface mount 表面贴装
Case 封装:SMBF



■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	V
DC Reverse Voltage 直流反向电压	V_R	100	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	70	V
Forward Rectified Current 正向整流电流	I_F	5	A
Peak Surge Current 峰值浪涌电流	I_{FSM}	120	A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	25	℃/W
Junction Temperature 结温	T_J	150	℃
Storage Temperature 储藏温度	T_{stg}	-55to+150℃	

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F	0.67	V	I_F=5A
Reverse Current 反向电流	I_R	0.1 20	mA	V_R=V_{RRM}(@25℃) (@125℃)
Diode Capacitance 二极管电容	C_D	370	pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

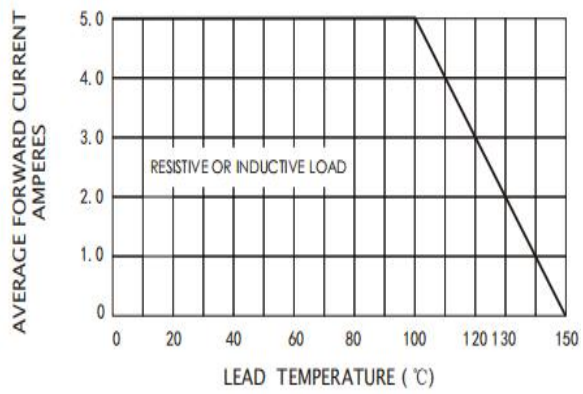


Figure 1: Forward Current Derating Curve

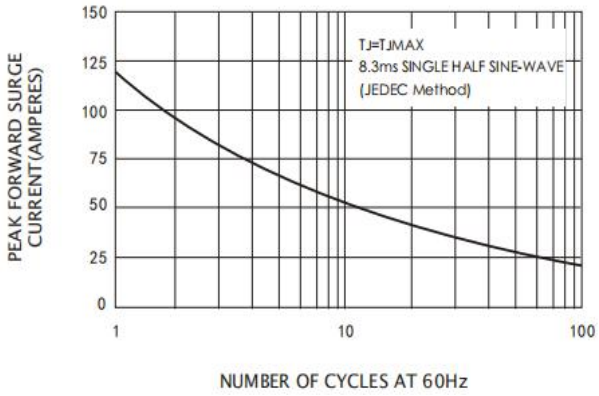


Figure 2: Peak Surge Current

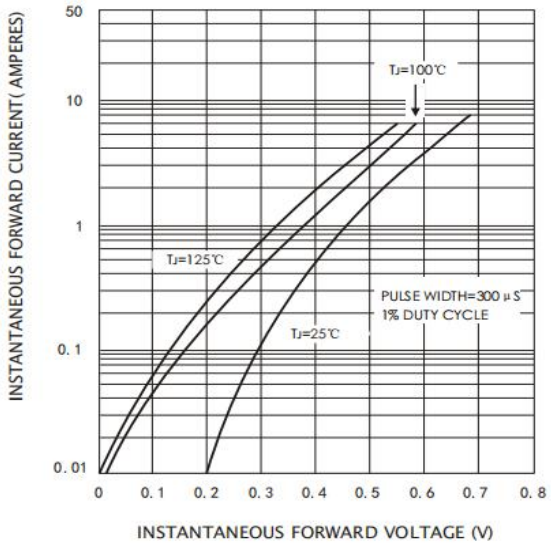


Figure 3: Forward Characteristics

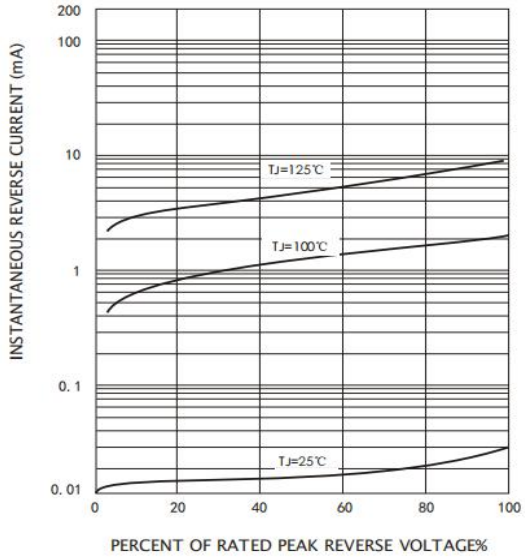


Figure 4: Reverse Characteristics

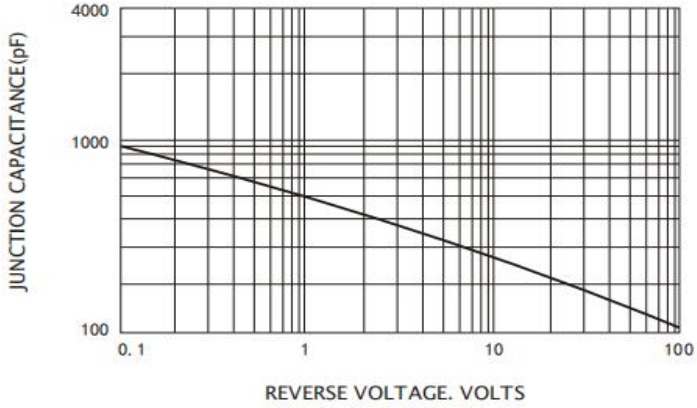
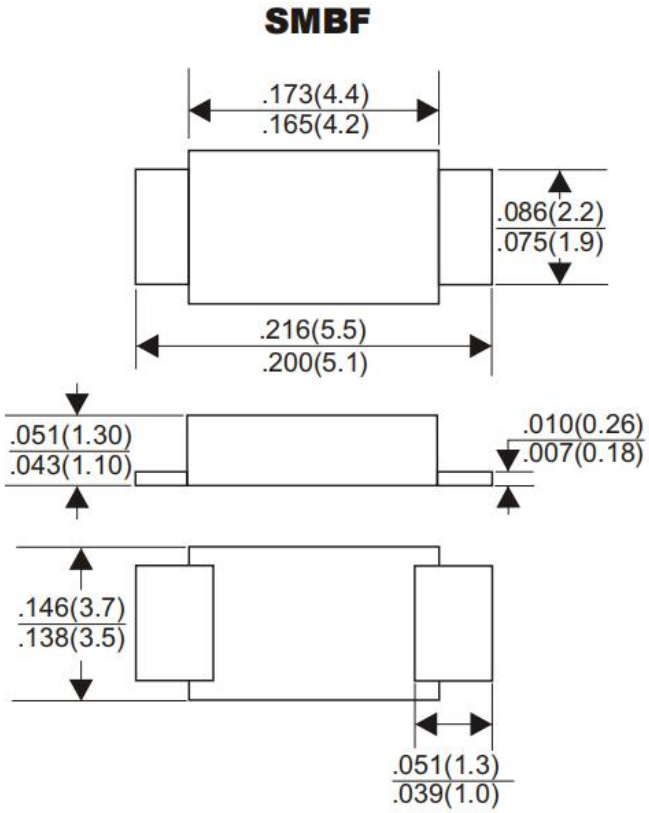


Figure 5: Capacitance Characteristics

■**Dimension 外形封装尺寸**



Dimensions in inches and (millimeters)